

# **isc Silicon NPN Power Transistor**

## **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min.)
- Wide Area of Safe Operation
- Complement to Type 2SB1187
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

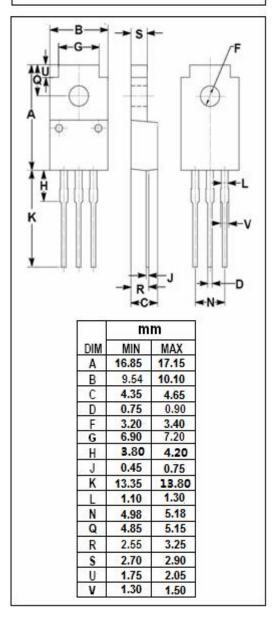
# PIN 1. BASE 2.COLLECTOR 3. BMITTER TO-220Fa package

# **APPLICATIONS**

• Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	80	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous	3	Α	
Ісм	Collector Current-Peak	6	Α	
P <sub>C</sub>	Collector Power Dissipation @ $T_a$ =25°C	2	W	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	30		
TJ	Junction Temperature 150		$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}\!\mathbb{C}$	





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2SD1761

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	60			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 50 μ A; I <sub>E</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50 μ A; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			10	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			10	μА
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	60		320	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1MHz		90		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>E</sub> = 0.5A; V <sub>CE</sub> = 5V		8		MHz

### h<sub>FE</sub> Classifications

D	E	F
60-120	100-200	160-320

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